

描述 / Descriptions

TO-220F 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-220F Plastic Package.

特征 / Features

RDS(on)的典型值是 0.15Ω,低电容,开关速度快。

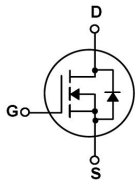
Typical RDS(on)=0.15Ω, low intrinsic capacitance C_{iss} , fast switching.

用途 / Applications

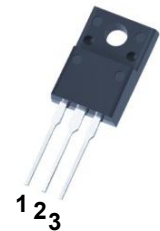
显示器监控,不间断电源,DC-DC 转换。

Monitor displays, UPS, DC-DC converters.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : G

PIN 2 : D

PIN 3 : S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

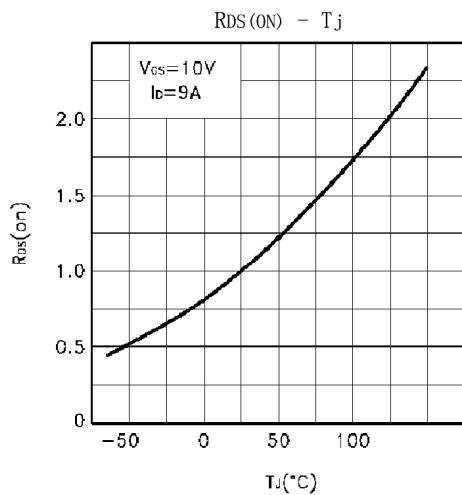
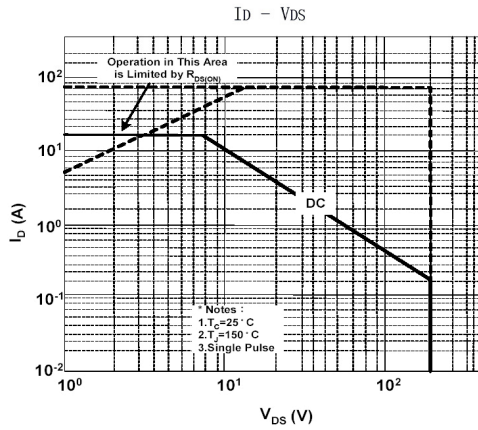
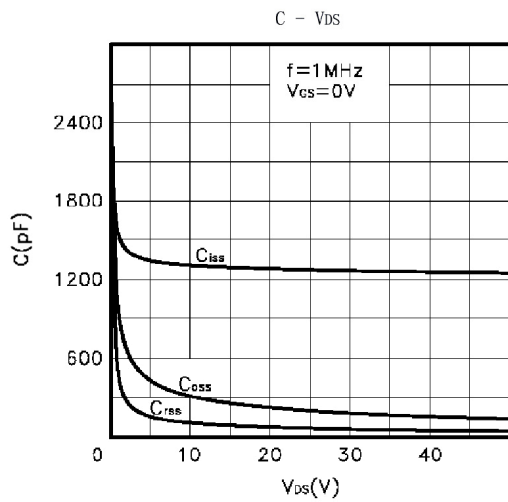
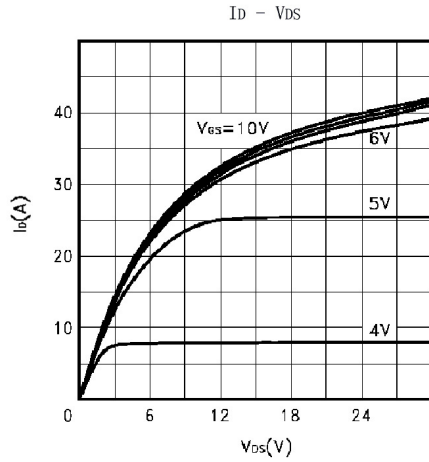
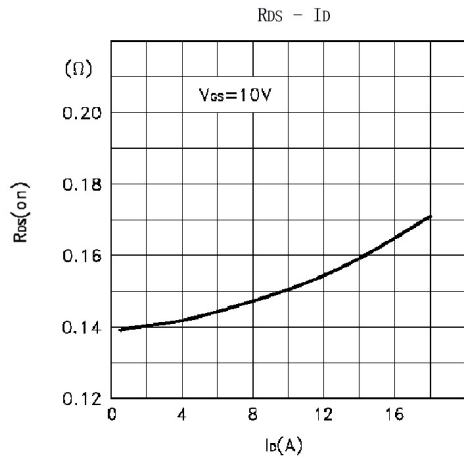
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	200	V
Drain-gate Voltage	V_{DGR}	200	V
Gate-Source Voltage	V_{GS}	±30	V
Drain Current	$I_D(T_c=25^{\circ}C)$	20	A
Drain Current - Pulsed	I_{DM}	72	A
Total Power Dissipation	P_{TOT}	40	W
Insulation Withstand Voltage	V_{ISO}	2500	V
Junction Temperature Range	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

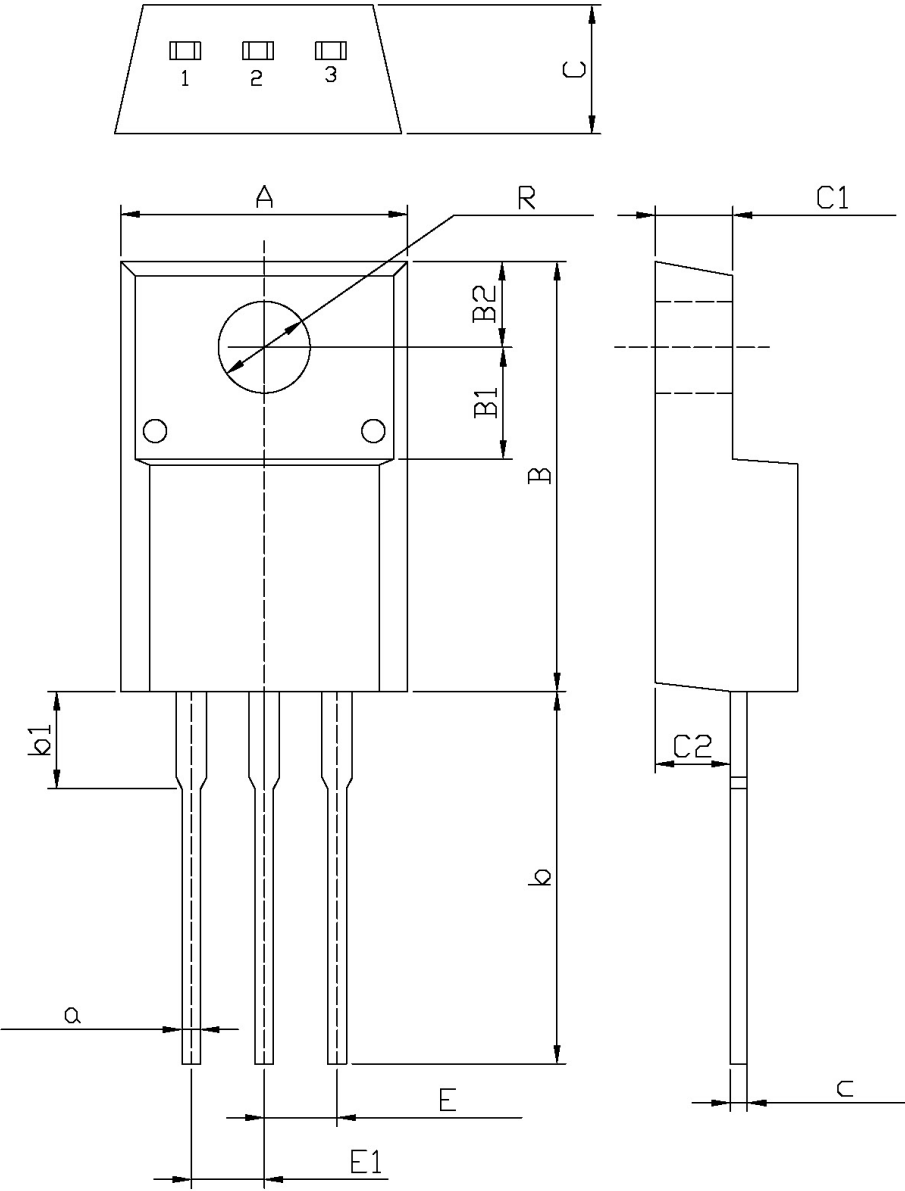
参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0	3.0	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=12A$		0.15	0.18	Ω
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=200V$ $V_{GS}=0V$			10	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=30V$ $V_{DS}=0V$			100	nA
		$V_{GS}=-30V$ $V_{DS}=0V$			-100	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_{SD}=12A$ $T_j=25^{\circ}C$			1.3	V
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=20V$ $f=1.0MHz$		900		pF
Output Capacitance	C_{oss}			180		
Reverse Transfer Capacitance	C_{rss}			70		

电参数曲线图 / Electrical Characteristic Curve



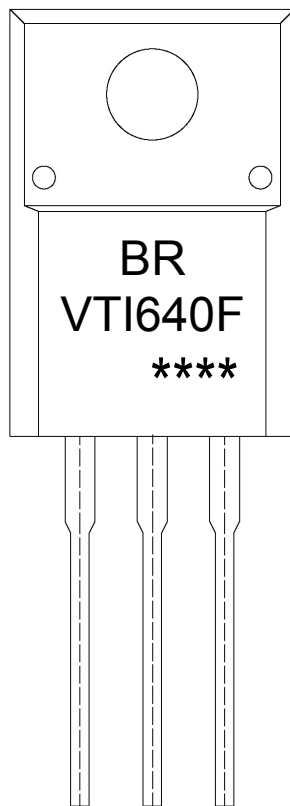
外形尺寸图 / Package Dimensions

T□-220F 单位：mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
B1	3.8	4.0	E1	2.29	2.79
B2	2.9	3.1	C1	2.5	2.9
R	3.0	3.4	C2	2.5	2.7
b	12.5	13.5	c	0.5	0.7

印章说明 / Marking Instructions



说明：

BR： 为公司代码

VTI640F： 为产品型号

****： 为生产批号代码，随生产批号变化。

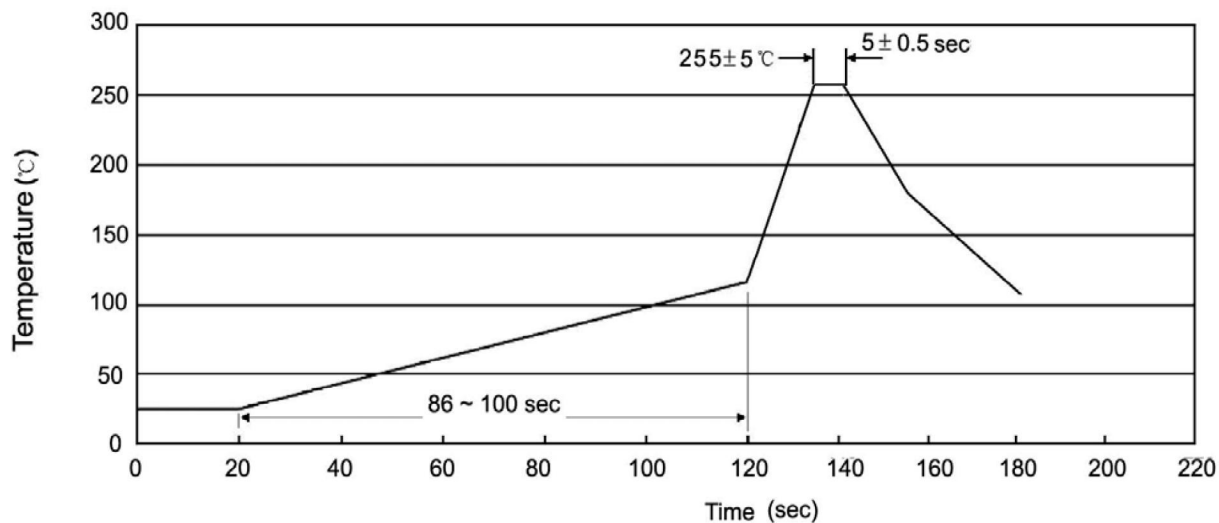
Note:

BR: Company Code

VTI640F: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices